

2SA1698

Silicon PNP Epitaxial Planar Type

General Amplifier

Complementary Pair with 2SC2258

■ Feature

- High collector-emitter voltage (V_{CE0})

■ Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	-300	V
Collector-emitter voltage	V_{CEO}	-300	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-100	mA
Collector current	I_C	-70	mA
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CEO}	$V_{CE} = -120V, I_B = 0$			-1	μA
Collector-emitter voltage	V_{CEO}	$I_C = -100\mu A, I_B = 0$	-300			V
Emitter-base voltage	V_{EBO}	$I_E = -1\mu A, I_C = 0$	-5			V
DC current gain	h_{FE}^*	$V_{CE} = -10V, I_C = -5mA$	30		220	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-1.5	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 10mA, f = 200MHz$	50	80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$			10	pF

*h_{FE} Classifications

Class	P	Q	R
h_{FE}	30~100	60~150	100~220

■ Package Dimensions





